**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- · Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

# 3. Applications

- Relay driver
- · High-speed line driver
- · Low-side load switch
- · Switching circuits

### 4. Quick reference data

#### Table 1. Quick reference data

| Symbol            | Parameter                        | Conditions   |     | Min | Тур      | Max | Unit |
|-------------------|----------------------------------|--|-----|-----|----------|-----|------|
| V <sub>DS</sub>   | drain-source voltage             | T <sub>j</sub> = 25 °C   |     | -   | -        | 60  | V    |
| V <sub>GS</sub>   | gate-source voltage              |  |     | -20 | -        | 20  | V    |
| I <sub>D</sub>    | drain current                    | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C                   | [1] | -   | -        | 270 | mA   |
|                   |                                  | V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C                    |     | -   | -        | 330 | mA   |
| Static charac     | teristics                        |  |     |     | <u>'</u> | '   |      |
| R <sub>DSon</sub> | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 200 \text{ mA}; T_j = 25 \text{ °C}$ |     | -   | 2.2      | 2.8 | Ω    |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



**60 V, N-channel Trench MOSFET** 

# 5. Pinning information

#### **Table 2. Pinning information**

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1   | G      | gate        | 3                  | D              |
| 2   | S      | source      |                    |                |
| 3   | D      | drain       | SOT23              | G S 017aaa255  |

# 6. Ordering information

### **Table 3. Ordering information**

| Type number | Package |  |         |  |  |  |
|-------------|---------|--|---------|--|--|--|
|             | Name    | Description  | Version |  |  |  |
| 2N7002NXBK  |         | plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body | SOT23   |  |  |  |

# 7. Marking

#### Table 4. Marking codes

| Type number | Marking code[1] |
|-------------|-----------------|
| 2N7002NXBK  | %4R             |

[1] % = placeholder for manufacturing site code

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# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions  |     | Min | Max  | Unit |
|------------------|-------------------------|---|-----|-----|------|------|
| $V_{DS}$         | drain-source voltage    | T <sub>j</sub> = 25 °C                              |     | -   | 60   | V    |
| $V_{GS}$         | gate-source voltage     |   |     | -20 | 20   | V    |
| I <sub>D</sub>   | drain current           | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C    | [1] | -   | 270  | mA   |
|                  |                         | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C   | [1] | -   | 170  | mA   |
|                  |                         | V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C     |     | -   | 330  | mA   |
| I <sub>DM</sub>  | peak drain current      | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$ |     | -   | 0.9  | Α    |
| P <sub>tot</sub> | total power dissipation | T <sub>amb</sub> = 25 °C                            | [2] | -   | 310  | mW   |
|                  |                         |   | [1] | -   | 400  | mW   |
|                  |                         | T <sub>sp</sub> = 25 °C                             |     | -   | 1670 | mW   |
| Tj               | junction temperature    |   |     | -55 | 150  | °C   |
| T <sub>amb</sub> | ambient temperature     |   |     | -55 | 150  | °C   |
| T <sub>stg</sub> | storage temperature     |   |     | -65 | 150  | °C   |
| Source-drai      | n diode                 |   | •   |     |      | •    |
| Is               | source current          | T <sub>amb</sub> = 25 °C                            | [1] | -   | 200  | mA   |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

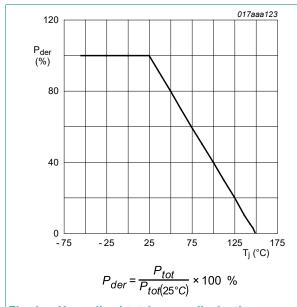


Fig. 1. Normalized total power dissipation as a function of junction temperature

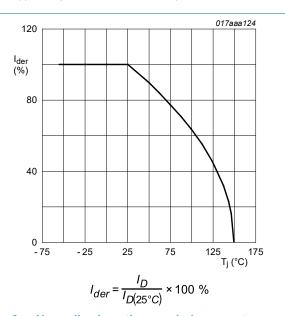
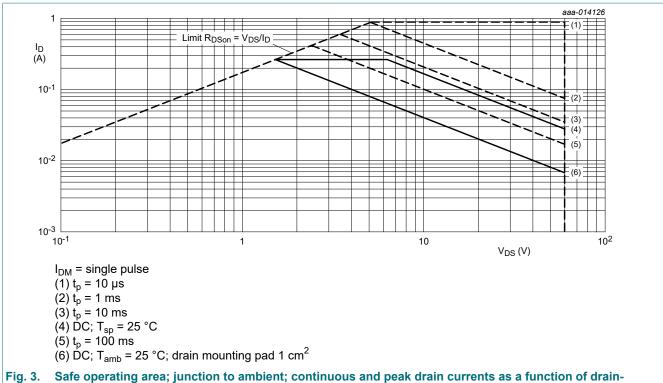


Fig. 2. Normalized continuous drain current as a function of junction temperature

#### 60 V, N-channel Trench MOSFET



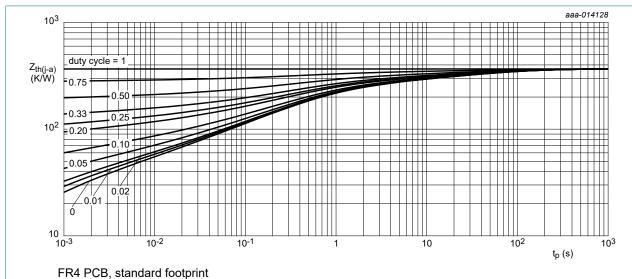
**60 V, N-channel Trench MOSFET** 

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

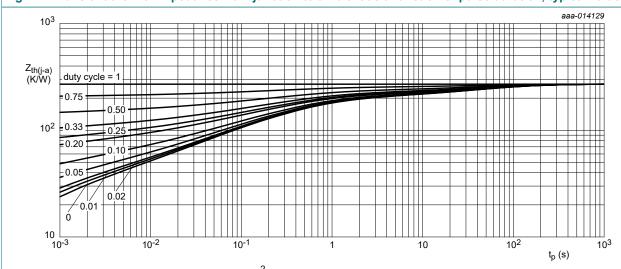
| Symbol                | Parameter  | Conditions  |     | Min | Тур | Max | Unit |
|-----------------------|--|-------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub>  | thermal resistance from                          | in free air | [1] | -   | 350 | 405 | K/W  |
| junction to ambient   |  | [2]         | -   | 270 | 310 | K/W |      |
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point |             |     | -   | 65  | 75  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



FR4 FGB, Standard 100tprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm<sup>2</sup>

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

**60 V, N-channel Trench MOSFET** 

# 10. Characteristics

#### **Table 7. Characteristics**

| Symbol               | Parameter                         | Conditions   | Min | Тур  | Max  | Unit |
|----------------------|-----------------------------------|--|-----|------|------|------|
| Static chara         | acteristics                       |  |     |      |      |      |
| V <sub>(BR)DSS</sub> | drain-source<br>breakdown voltage | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C   | 60  | -    | -    | V    |
| $V_{GSth}$           | gate-source threshold voltage     | $I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$                  | 1.1 | 1.6  | 2.1  | V    |
| I <sub>DSS</sub>     | drain leakage current             | V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C    | -   | -    | 1    | μA   |
| I <sub>GSS</sub>     | gate leakage current              | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C    | -   | -    | 10   | μA   |
|                      |                                   | V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C   | -   | -    | -10  | μΑ   |
|                      |                                   | V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C    | -   | -    | 1    | μΑ   |
|                      |                                   | V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C   | -   | -    | -1   | μΑ   |
|                      |                                   | V <sub>GS</sub> = 5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C     | -   | -    | 0.3  | μΑ   |
|                      |                                   | V <sub>GS</sub> = -5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C    | -   | -    | -0.3 | μΑ   |
| R <sub>DSon</sub>    | drain-source on-state resistance  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C  | -   | 2.2  | 2.8  | Ω    |
|                      |                                   | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 150 °C | -   | 4.5  | 5.7  | Ω    |
|                      |                                   | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C   | -   | 2.5  | 3.2  | Ω    |
| 9 <sub>fs</sub>      | forward transconductance          | $V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}; T_j = 25 \text{ °C}$       | -   | 600  | -    | mS   |
| R <sub>G</sub>       | gate resistance                   | f = 2.5 MHz  | -   | 2.5  | -    | Ω    |
| Dynamic ch           | naracteristics                    |  | '   |      |      |      |
| Q <sub>G(tot)</sub>  | total gate charge                 | V <sub>DS</sub> = 30 V; I <sub>D</sub> = 200 mA; V <sub>GS</sub> = 10 V; | -   | 1    | -    | nC   |
| Q <sub>GS</sub>      | gate-source charge                | T <sub>j</sub> = 25 °C   | -   | 0.12 | -    | nC   |
| $Q_{GD}$             | gate-drain charge                 |  | -   | 0.18 | -    | nC   |
| C <sub>iss</sub>     | input capacitance                 | V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;                | -   | 23.6 | -    | pF   |
| C <sub>oss</sub>     | output capacitance                | T <sub>j</sub> = 25 °C   | -   | 4.6  | -    | pF   |
| C <sub>rss</sub>     | reverse transfer capacitance      |  | -   | 3    | -    | pF   |
| t <sub>d(on)</sub>   | turn-on delay time                | V <sub>DS</sub> = 50 V; I <sub>D</sub> = 200 mA; V <sub>GS</sub> = 10 V; | -   | 4.7  | -    | ns   |
| t <sub>r</sub>       | rise time                         | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$                                     | -   | 4.3  | -    | ns   |
| t <sub>d(off)</sub>  | turn-off delay time               | ]  | -   | 6.9  | -    | ns   |
| t <sub>f</sub>       | fall time                         |  | -   | 2.9  | -    | ns   |
| Source-dra           | in diode                          |  | '   |      |      |      |
| $V_{SD}$             | source-drain voltage              | I <sub>S</sub> = 200 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C   | -   | 0.87 | 1.2  | V    |

#### **60 V, N-channel Trench MOSFET**

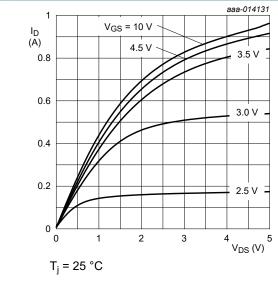
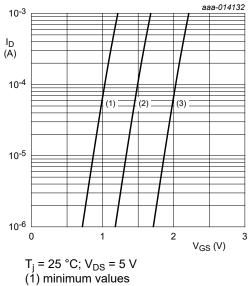


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



- (2) typical values
- (3) maximum values

Sub-threshold drain current as a function of Fig. 7. gate-source voltage

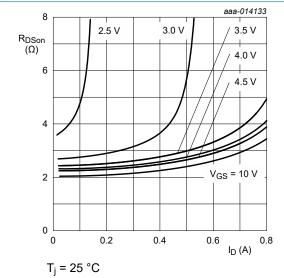
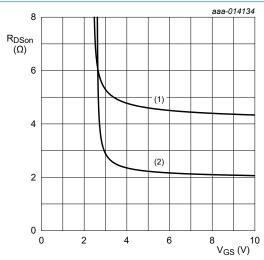


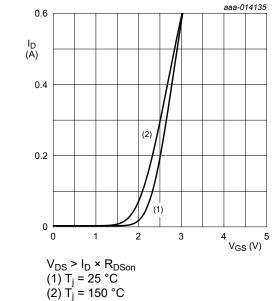
Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

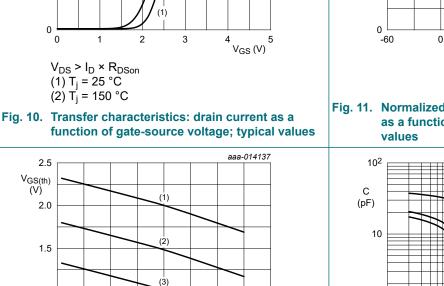


 $I_D = 0.2 A$ (1)  $T_j = 150 \, ^{\circ}C$ (2)  $T_j = 25 \,^{\circ}\text{C}$ 

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 60 V, N-channel Trench MOSFET





180

T<sub>j</sub> (°C)

 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$ 

- (1) maximum values
- (2) typical values

1.0

0.5

(3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature

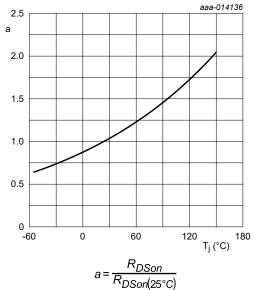
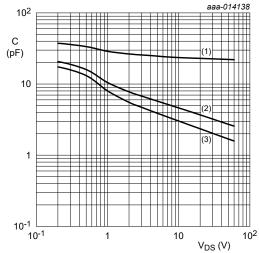


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### **60 V, N-channel Trench MOSFET**

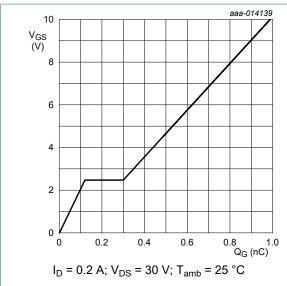


Fig. 14. Gate-source voltage as a function of gate charge; typical values

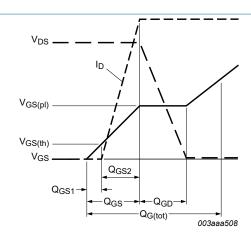
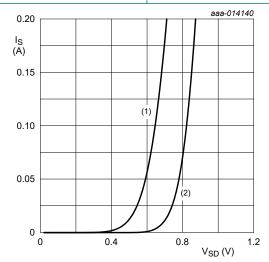


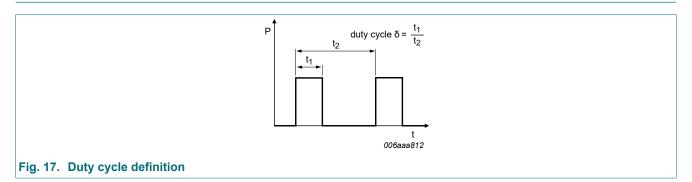
Fig. 15. Gate charge waveform definitions



 $V_{GS} = 0 V$ (1)  $T_j = 150 \,^{\circ}C$ (2)  $T_j = 25 \,^{\circ}C$ 

Fig. 16. Source current as a function of source-drain voltage; typical values

### 11. Test information



2N7002NXBK

#### 60 V, N-channel Trench MOSFET

# 12. Package outline

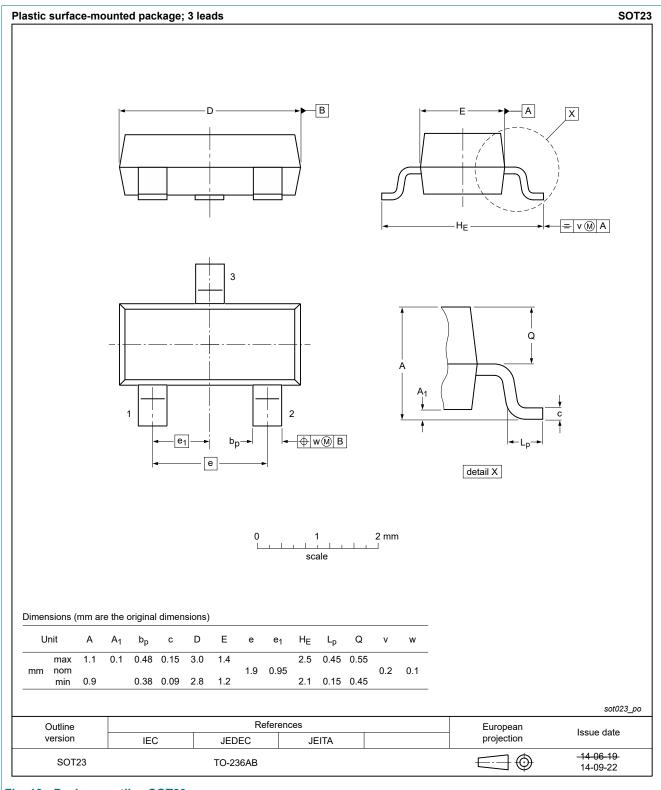
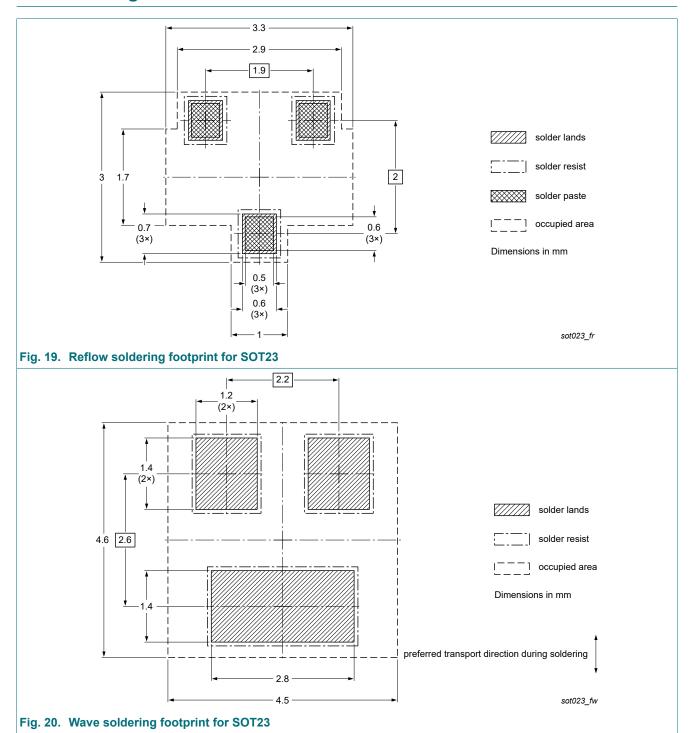


Fig. 18. Package outline SOT23

**60 V, N-channel Trench MOSFET** 

# 13. Soldering



**60 V, N-channel Trench MOSFET** 

# 14. Revision history

#### **Table 8. Revision history**

| Data sheet ID  | Release date  | Data sheet status  | Change notice | Supersedes     |  |  |  |
|----------------|---|--------------------|---------------|----------------|--|--|--|
| 2N7002NXBK v.2 | 20190725  | Product data sheet | -             | 2N7002NXBK v.1 |  |  |  |
| Modification   | Corrected the package information from SOT89 to SOT23 |                    |               |                |  |  |  |
| 2N7002NXBK v.1 | 20190701  | Product data sheet | -             | -              |  |  |  |

#### 60 V, N-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

| Document status [1][2]         | Product<br>status [3] | Definition  |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet   | Development           | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification         | This document contains data from the preliminary specification.                       |
| Product [short]<br>data sheet  | Production            | This document contains the product specification.                                     |

- Please consult the most recently issued document before initiating or completing a design.
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2N7002NXBK

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### **60 V, N-channel Trench MOSFET**

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